

Silicon NPN Power Transistors

2SD627

DESCRIPTION

- With TO-3 package
- High voltage,high speed

APPLICATIONS

- For use in horizontal deflection output stages for color TV receivers

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

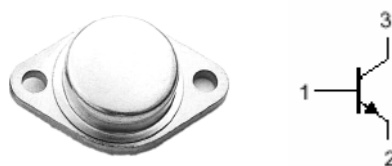


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		6	A
P_C	Collector power dissipation	$T_C = 25\square$	50	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-45~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$	600			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2.5A$; $I_B=0.6A$			10	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2.5A$; $I_B=0.6A$			1.6	V
I_{CBO}	Collector cut-off current	$V_{CB}=1000V$; $I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V$; $I_C=0$			1.0	mA
h_{FE}	DC current gain	$I_C=2A$; $V_{CE}=10V$	5		25	
t_f	Fall time	$I_{CP}=2.5A$			1.0	μs

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PACKAGE OUTLINE

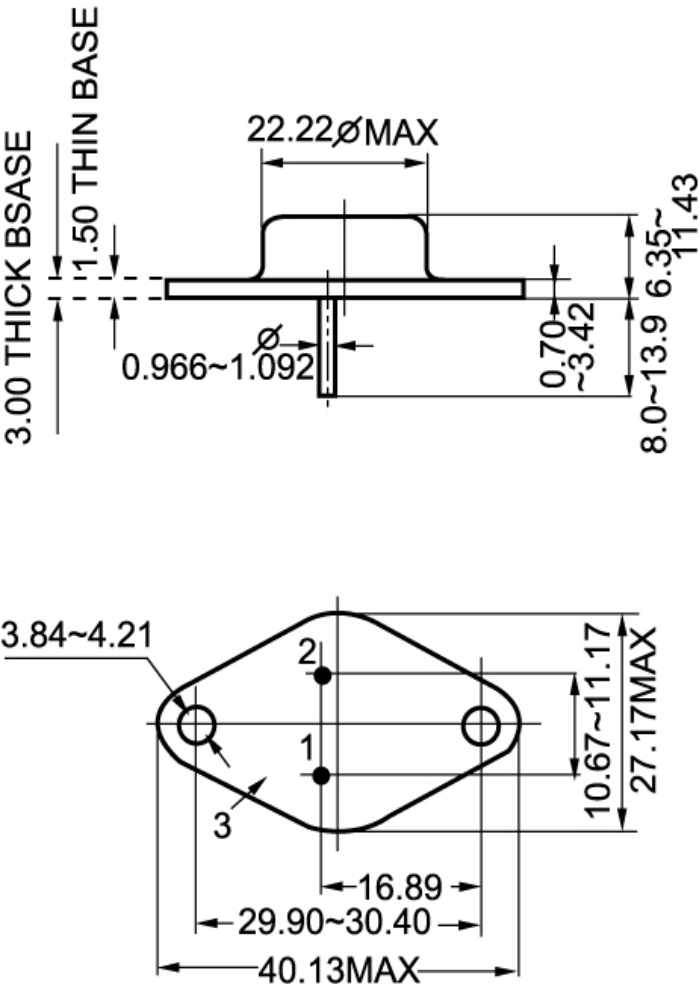


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)